

TOSHIBA DIODE SILICON EPITAXIAL SCHOTTKY BARRIER TYPE

1SS367

HIGH SPEED SWITCHING APPLICATION

- Small Package
- Low Forward Voltage :  $V_F = 0.23V$  (TYP.) @  $I_F = 5mA$

MAXIMUM RATINGS ( $T_a = 25^\circ C$ )

| CHARACTERISTIC                 | SYMBOL     | RATING         | UNIT       |
|--------------------------------|------------|----------------|------------|
| Maximum (Peak) Reverse Voltage | $V_{RM}$   | 15             | V          |
| Reverse Voltage                | $V_R$      | 10             | V          |
| Maximum (Peak) Forward Current | $I_{FM}$   | 200            | mA         |
| Average Forward Current        | $I_O$      | 100            | mA         |
| Surge Current (10ms)           | $I_{FSM}$  | 1              | A          |
| Power Dissipation              | $P_{\ast}$ | 200            | mW         |
| Junction Temperature           | $T_j$      | 125            | $^\circ C$ |
| Storage Temperature Range      | $T_{stg}$  | $-55 \sim 125$ | $^\circ C$ |
| Operating Temperature Range    | $T_{opr}$  | $-40 \sim 100$ | $^\circ C$ |

Unit in mm

|         |        |
|---------|--------|
| USC     |        |
| JEDEC   | —      |
| EIAJ    | —      |
| TOSHIBA | 1-1E1A |

Weight : 0.004g

※ Mounted on a glass epoxy circuit board of 20×20mm Pad dimension of 4×4mm.

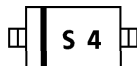
ELECTRICAL CHARACTERISTICS ( $T_a = 25^\circ C$ )

| CHARACTERISTIC    | SYMBOL     | TEST CONDITION      | MIN. | TYP. | MAX. | UNIT    |
|-------------------|------------|---------------------|------|------|------|---------|
| Forward Voltage   | $V_{F(1)}$ | $I_F = 1mA$         | —    | 0.18 | —    | V       |
|                   | $V_{F(2)}$ | $I_F = 5mA$         | —    | 0.23 | 0.30 |         |
|                   | $V_{F(3)}$ | $I_F = 100mA$       | —    | 0.35 | 0.50 |         |
| Reverse Current   | $I_R$      | $V_R = 10V$         | —    | —    | 20   | $\mu A$ |
| Total Capacitance | $C_T$      | $V_R = 0, f = 1MHz$ | —    | 20   | 40   | pF      |

EQUIVALENT CIRCUIT (TOP VIEW)



MARKING



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